



# Frontiers of Excellence in Wide and Ultrawide Bandgap Semiconductors and Electronic Systems

Indian Institute of Technology Bombay, Mumbai  
December 14 - 15, 2019

## Organizing committee

### IIT Bombay

Prof. Saurabh Lodha  
Prof. Swaroop Ganguly

### OSU

Prof. Siddharth Rajan  
Prof. Steven Ringel

### Plenary Talks

Prof. Patrick Fay (Univ. of Notre Dame)  
Prof. Uttam Singiseti (Univ. at Buffalo)  
Prof. Jin Wang (OSU)  
Prof. B.G. Fernandes (IITB)  
Dr. Apurba Bhattacharya (ISRO)  
Dr. Seema Vinayak (SSPL)

### Invited Talks

Prof. Saurabh Lodha (IITB)  
Prof. Dipankar Saha (IITB)  
Prof. Subhabrata Dhar (IITB)  
Prof. Apurba Laha (IITB)  
Prof. Himanshu Bahirat (IITB)  
Prof. Anshuman Shukla (IITB)  
Prof. Siddharth Rajan (OSU)  
Prof. Steven Ringel (OSU)  
Prof. Wu Lu (OSU)  
Prof. Hongping Zhao (OSU)  
Prof. Amitava Dasgupta (IITM)  
Prof. Kamalesh Hatua (IITM)  
Prof. Digbijoy Nath (IISc)  
Prof. Subhashish Bhattacharya (NCSU)  
Dr. Amitava Das (Tagore Technology)  
Dr. D. Krishnamurthy (SHANAN Innovetek Ventures)

### Contact us:

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[Indian Institute of Technology, Bombay](#) (IITB), and [Ohio State University](#) (OSU) are jointly organizing an Indo-US workshop on “Frontiers of Excellence in Wide & Ultrawide Bandgap Semiconductors and Electronic Systems” during December 14-15, 2019. This workshop is sponsored by [Indo-US Science and Technology Forum](#) (IUSSTF), an organization set up by the Indian and the US governments to promote collaboration and interaction between Indian and US scientists. Wide band gap materials and devices are a key thrust area today due to their applications in energy-efficient power electronics, high frequency communications and solid state lighting. These applications coupled with a strong thrust and policy framework from both the Indian and the US governments, makes this workshop timely and relevant.

IITB and OSU are well known centers of excellence in (ultra) wide bandgap semiconductor research. This joint workshop will benefit research, development, and deployment of power semiconductor devices and power electronics technologies in the immediate future in both countries. This workshop intends to bring together academia and industry working on this area for better understanding, exchanging information, and brainstorming ideas on challenges and opportunities in state-of-the-art power devices and power electronic systems.

This event will focus on overviews of materials, devices and electronics for a range of established and emerging technologies (e.g. Si, SiC, GaN, Ga<sub>2</sub>O<sub>3</sub>, diamond). The technical programme includes the following thematic areas:

- Gallium Nitride Growth and Devices
- Gallium Nitride Power and RF Devices
- Gallium Oxide Growth and Defects
- Gallium Oxide Devices
- Wide Band Gap Power Electronics

It is expected that there will be about 20 speakers from academia and industry from India and USA. The sessions will focus on in-depth presentations of new results pertaining to these technologies – especially material growth and quality, novel device designs as well as power electronic system challenges.

Online applications are invited from interested researchers from academia, R&D laboratories, and industries for participation in this workshop. A limited number of applicants from academia (especially doctoral students) will be provided financial assistance for travel, accommodation and local hospitality. We also encourage self-supported participants for this workshop.

[CLICK HERE TO REGISTER](#)

**Important dates: Registration deadline: November 27, 2019**  
**Confirmation of selection: November 29, 2019**